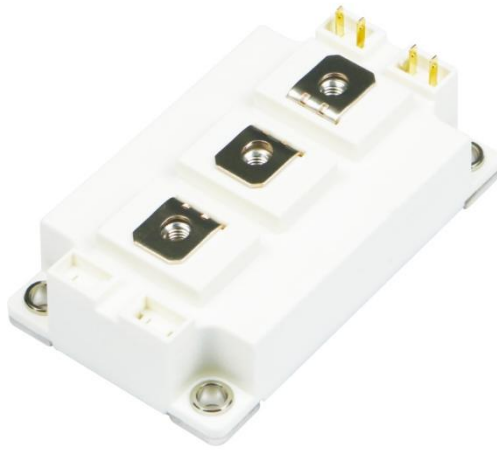




IGBT Modules

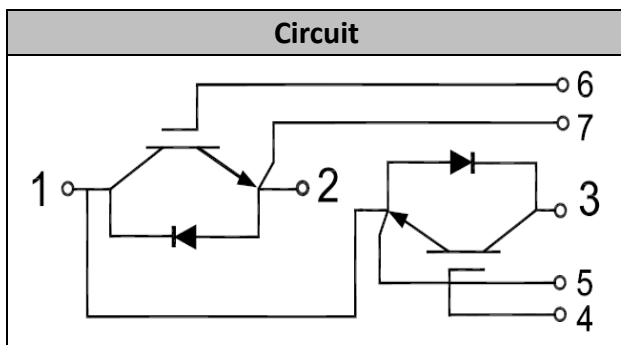
V_{CES}	1200V
I_C	300A

Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- UPS (Uninterruptible Power Supplies)
- Soft switching welding machine

Features

- Low $V_{CE(sat)}$ with Trench technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability(7us)
- Including ultra fast & soft recovery anti-parallel FWD
- Low inductance
- Maximum junction temperature 175°C



● IGBT

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	V_{CES}	$V_{GE}=0V, I_C=1mA, T_{vj}=25^{\circ}C$	1200	V
Continuous Collector Current	I_C	$T_C=100^{\circ}C$	300	A
Repetitive Peak Collector Current	I_{CRM}	$t_p=1ms$	600	A
Gate-Emitter Voltage	V_{GES}	$T_{vj}=25^{\circ}C$	± 20	V
Total Power Dissipation	P_{tot}	$T_C=25^{\circ}C$ $T_{vjmax}=175^{\circ}C$	1071	W



Characteristic Values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}$, $I_C=11.5mA$, $T_{vj}=25^{\circ}C$	5.2	5.9	6.4	V
Collector-Emitter Cut-off Current	I_{CES}	$V_{CE}=1200V$, $V_{GE}=0V$, $T_{vj}=25^{\circ}C$			1.0	mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=300A$, $V_{GE}=15V$, $T_{vj}=25^{\circ}C$		1.70		V
		$I_C=300A$, $V_{GE}=15V$, $T_{vj}=150^{\circ}C$		2.04		
		$I_C=300A$, $V_{GE}=15V$, $T_{vj}=175^{\circ}C$		2.10		
Gate Charge	Q_G			4.6		uC
Internal Gate Resistor	R_{Gint}			1.1		Ω
Input Capacitance	C_{ies}	$V_{CE}=25V$, $V_{GE}=0V$, $f=1MHz$, $T_{vj}=25^{\circ}C$		221		nF
Reverse Transfer Capacitance	C_{res}			0.45		nF
Gate-Emitter leakage current	I_{GES}	$V_{CE}=0V$, $V_{GE}=20V$, $T_{vj}=25^{\circ}C$			400	nA
Turn-on Delay Time	$t_{d(on)}$	$I_C=300A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=2.2\Omega$ $T_{vj}=25^{\circ}C$		132		ns
Rise Time	t_r			79		ns
Turn-off Delay Time	$t_{d(off)}$			325		ns
Fall Time	t_f			140		ns
Energy Dissipation During Turn-on Time	E_{on}			34.7		mJ
Energy Dissipation During Turn-off Time	E_{off}			18.8		mJ
Turn-on Delay Time	$t_{d(on)}$	$I_C=300A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=2.2\Omega$ $T_{vj}=150^{\circ}C$		140		ns
Rise Time	t_r			86		ns
Turn-off Delay Time	$t_{d(off)}$			368		ns
Fall Time	t_f			212		ns
Energy Dissipation During Turn-on Time	E_{on}			47.9		mJ
Energy Dissipation During Turn-off Time	E_{off}			25.0		mJ
Turn-on Delay Time	$t_{d(on)}$	$I_C=300A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=2.2\Omega$ $T_{vj}=175^{\circ}C$		142		ns
Rise Time	t_r			87		ns
Turn-off Delay Time	$t_{d(off)}$			376		ns
Fall Time	t_f			228		ns
Energy Dissipation During Turn-on Time	E_{on}			50.6		mJ
Energy Dissipation During Turn-off Time	E_{off}			26.7		mJ
SC Data	I_{sc}	$t_p \leq 7\mu s$, $V_{GE}=15V$, $T_{vj}=175^{\circ}C$, $V_{CC}=600V$, $V_{CEM} \leq 1200V$		1110		A



● Diode

Absolute Maximum Ratings

	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	$T_{vj}=25^{\circ}\text{C}$	1200	V
Continuous DC Forward Current	I_F		300	A
Repetitive Peak Forward Current	I_{FRM}	$t_p=1\text{ms}$	600	A

Characteristic Values

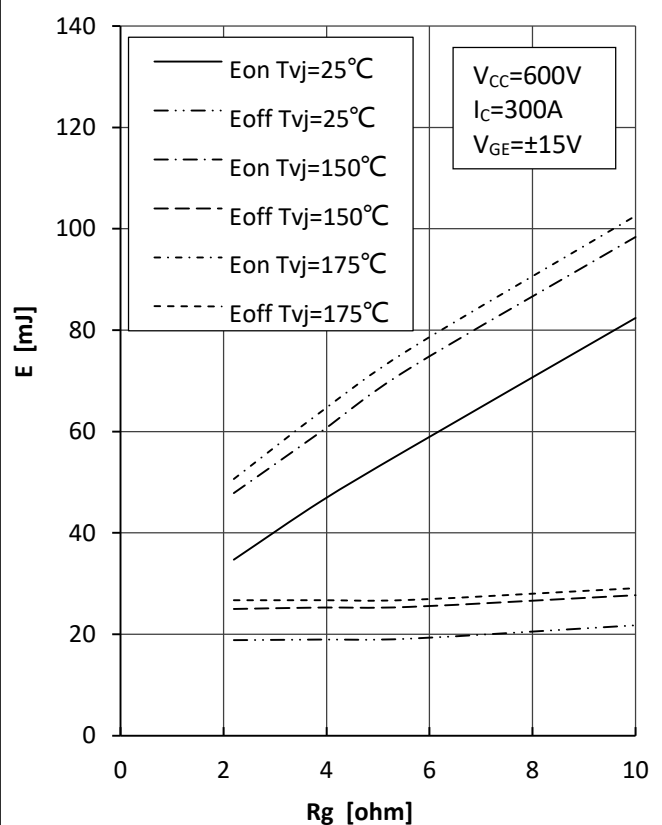
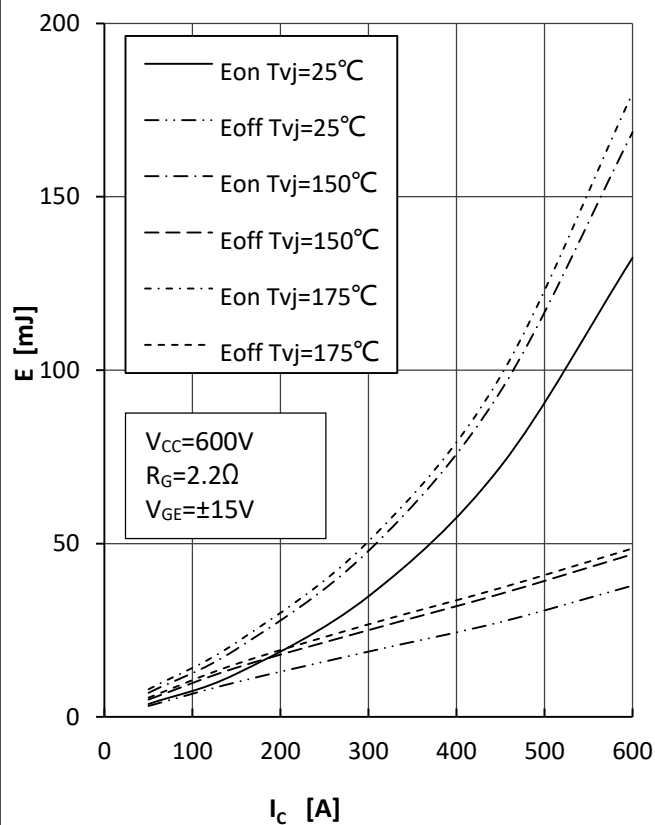
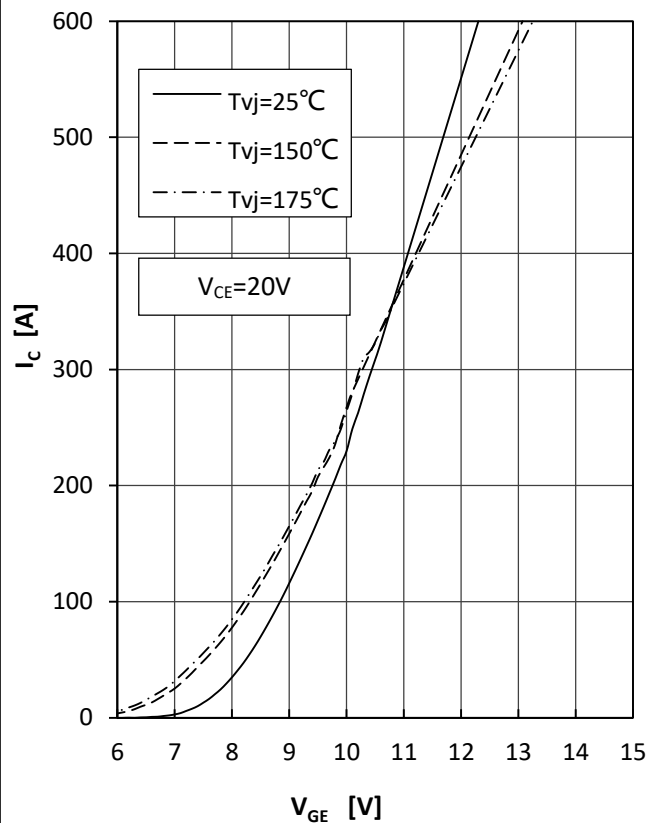
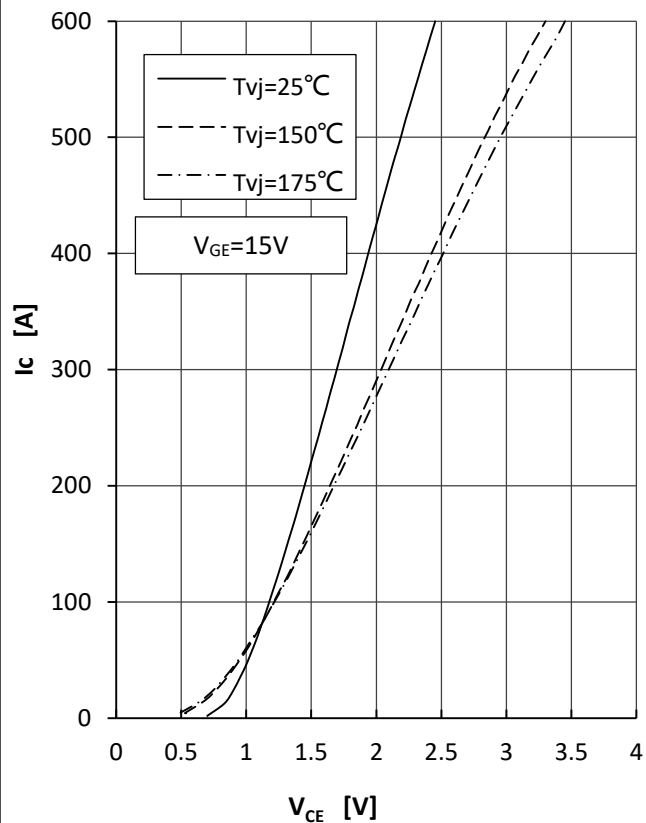
Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Forward Voltage	V_F	$I_F=300\text{A}, T_{vj}=25^{\circ}\text{C}$		2.35		V
		$I_F=300\text{A}, T_{vj}=150^{\circ}\text{C}$		1.88		
		$I_F=300\text{A}, T_{vj}=175^{\circ}\text{C}$		1.79		
Recovered Charge	Q_{rr}	$I_F=300\text{A}$		12.6		μC
Peak Reverse Recovery Current	I_{rr}	$V_R=600\text{V}$ $-di_F/dt=3100\text{A}/\mu\text{s}$		94.2		A
Reverse Recovery Energy	E_{rec}	$T_{vj}=25^{\circ}\text{C}$		3.6		mJ
Recovered Charge	Q_{rr}	$I_F=300\text{A}$		33.2		μC
Peak Reverse Recovery Current	I_{rr}	$V_R=600\text{V}$ $-di_F/dt=3100\text{A}/\mu\text{s}$		137.8		A
Reverse Recovery Energy	E_{rec}	$T_{vj}=150^{\circ}\text{C}$		10.1		mJ
Recovered Charge	Q_{rr}	$I_F=300\text{A}$		40.0		μC
Peak Reverse Recovery Current	I_{rr}	$V_R=600\text{V}$ $-di_F/dt=3100\text{A}/\mu\text{s}$		147.4		A
Reverse Recovery Energy	E_{rec}	$T_{vj}=175^{\circ}\text{C}$		12.3		mJ

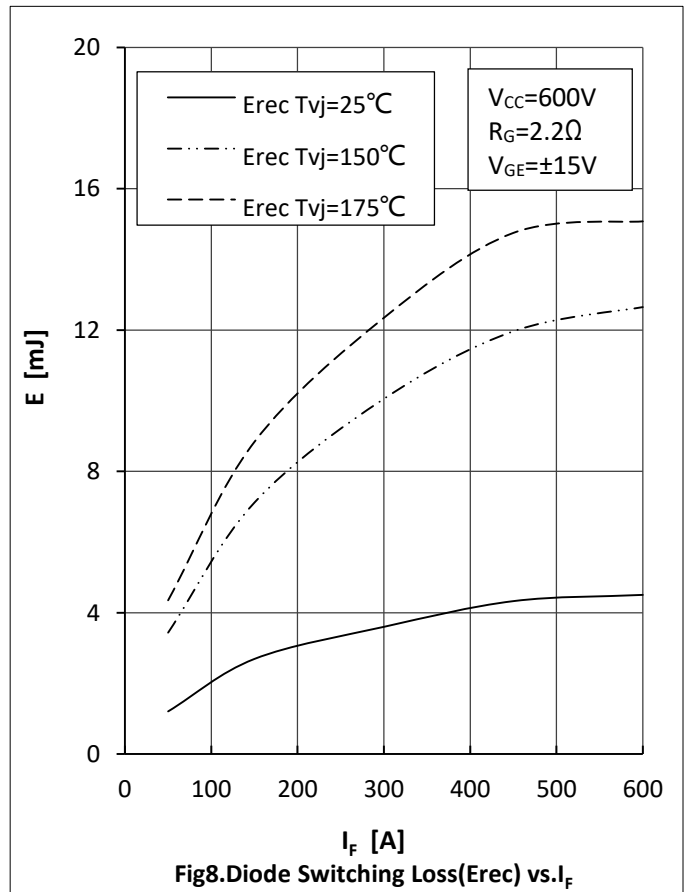
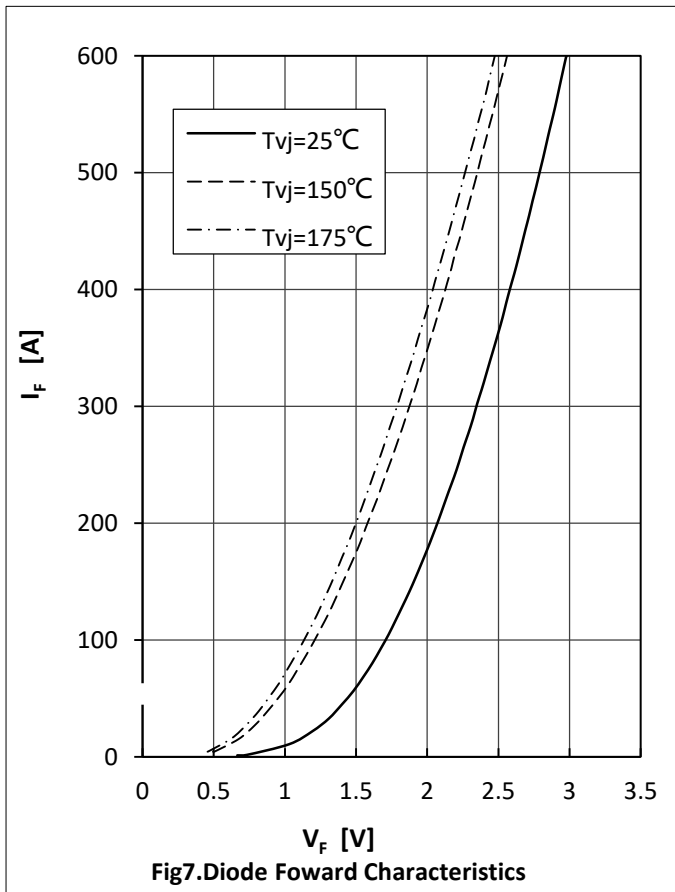
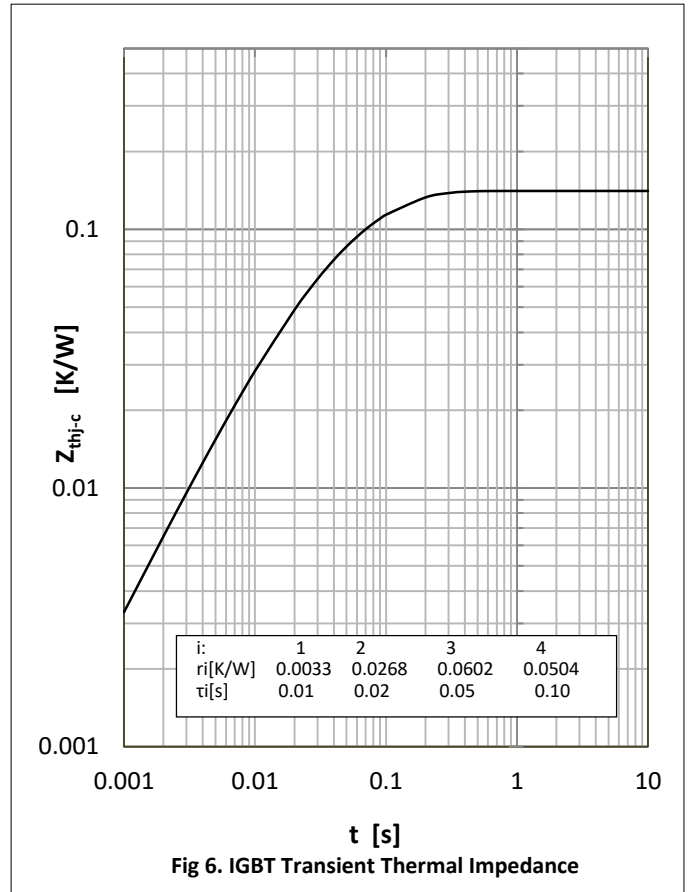
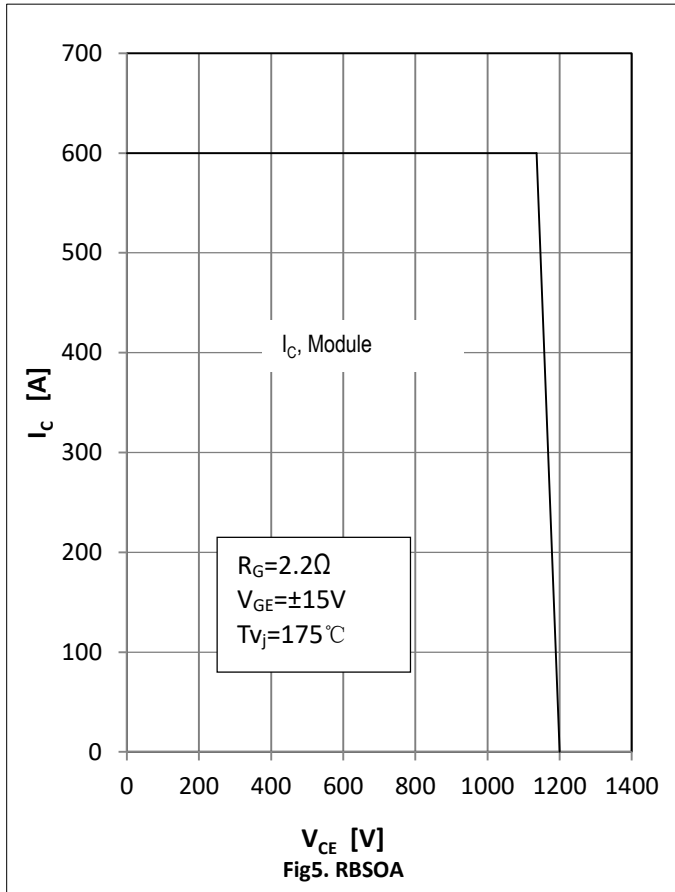


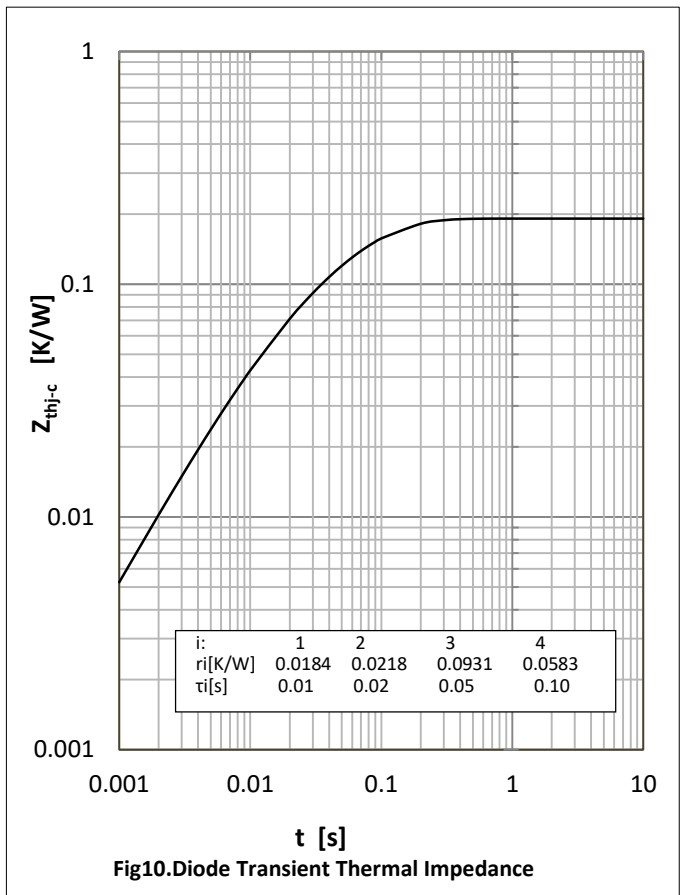
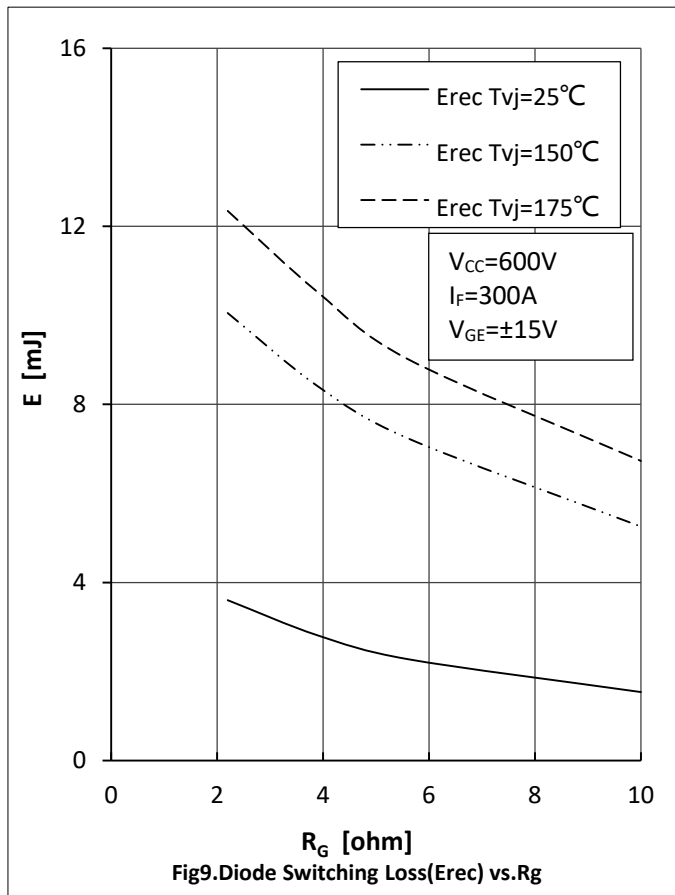
● Module Characteristics

$T_C=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Isolation Voltage	V_{isol}	$t=1\text{min}, f=50\text{Hz}$	2500			V
Maximum Junction Temperature	T_{jmax}				175	$^{\circ}\text{C}$
Operating Junction Temperature	$T_{\text{vj op}}$		-40		150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}		-40		125	$^{\circ}\text{C}$
Thermal Resistance Junction to Case	$R_{\theta\text{JC}}$	per IGBT			0.14	K/W
		per Diode			0.19	
Thermal Resistance Case to Sink	$R_{\theta\text{CS}}$	Conductive grease applied		0.012	0.035	K/W
Comparative Tracking Index	CTI		400			
Module Electrodes Torque	M_t	Recommended(M6)	3.0		5.0	N·m
Module to Sink Torque	M_s	Recommended(M6)	3.0		5.0	N·m
Weight of Module	G			315		g

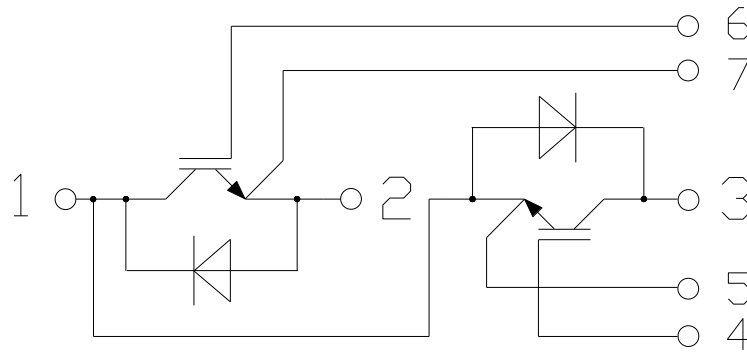






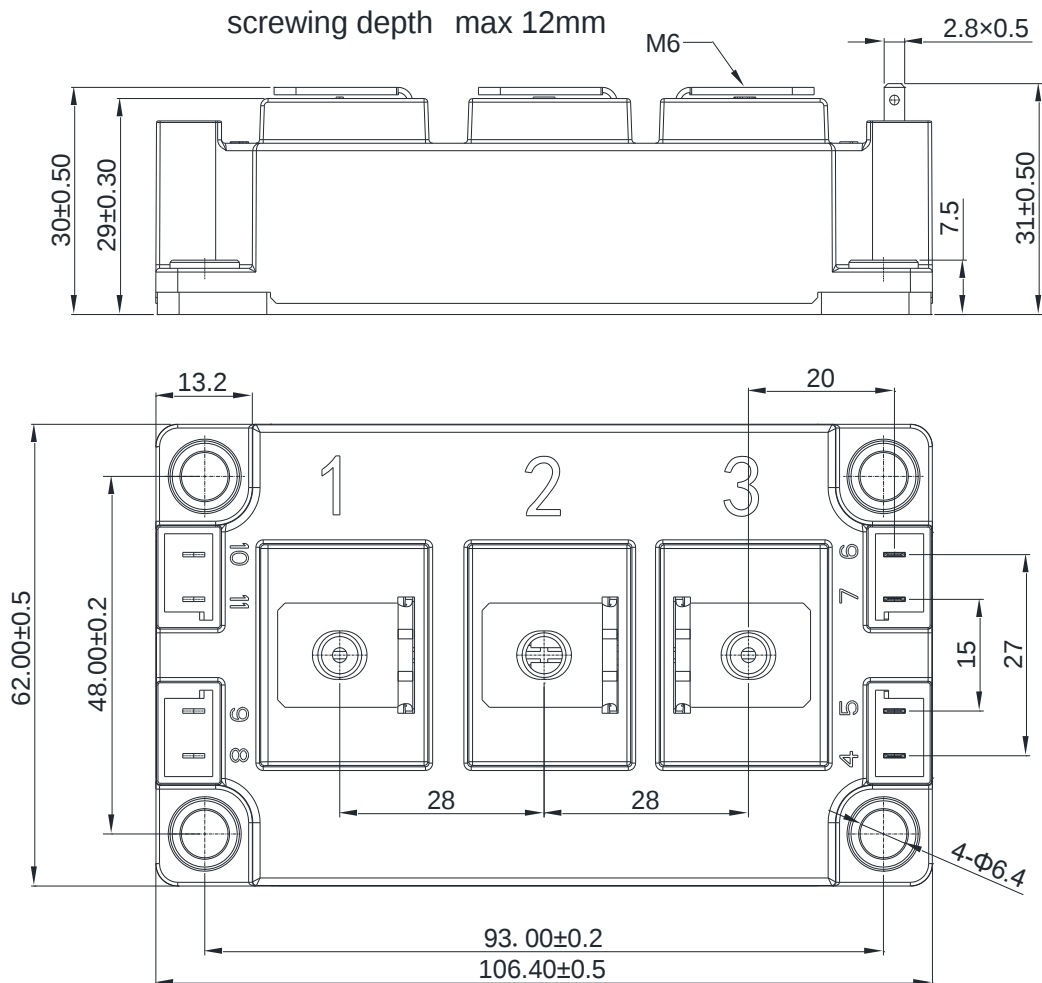


● Circuit Diagram



● Package Outline Information

Dimensions in Millimeters





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IGBTs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.

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